

High Efficiency Thyristor

$$V_{RRM} = 1200\text{ V}$$

$$I_{TAV} = 5\text{ A}$$

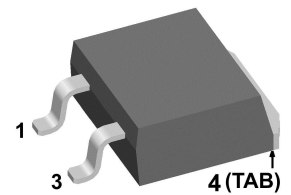
$$V_T = 1.31\text{ V}$$

Single Thyristor

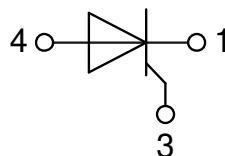
Part number

CLA5E1200PZ

Marking on Product: CLA5E1200PZ



Backside: anode



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-263 (D2Pak-HV)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- High creepage distance between terminals

Disclaimer Notice

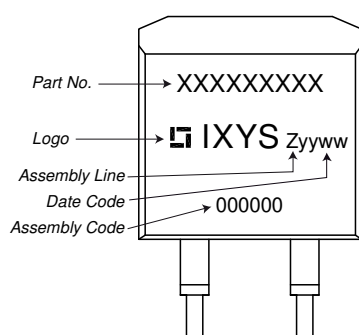
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Thyristor				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			10	μA
		$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			1	mA
V_T	forward voltage drop	$I_T = 5\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.33	V
		$I_T = 10\text{ A}$				1.62	V
		$I_T = 5\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.31	V
		$I_T = 10\text{ A}$				1.72	V
I_{TAV}	average forward current	$T_C = 135^{\circ}\text{C}$	$T_{VJ} = 150^{\circ}\text{C}$			5	A
$I_{T(RMS)}$	RMS forward current	180° sine				7.8	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}\text{C}$			0.89	V
r_T	slope resistance					85	m Ω
R_{thJC}	thermal resistance junction to case					1.5	K/W
R_{thCH}	thermal resistance case to heatsink				0.25		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			85	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			70	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			76	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			60	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			64	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			25	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			24	A ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			18	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			17	A ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		2		pF
P_{GM}	max. gate power dissipation	$t_P = 30\text{ }\mu\text{s}$	$T_C = 150^{\circ}\text{C}$			5	W
		$t_P = \text{ }\mu\text{s}$				2.5	W
P_{GAV}	average gate power dissipation					0.25	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 10\text{ A}$				150	A/ μs
		$t_P = 200\text{ }\mu\text{s}; di_G/dt = 0.1\text{ A}/\mu\text{s};$ $I_G = 0.1\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 5\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}\text{C}$			500	V/ μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1.8	V
			$T_{VJ} = -40^{\circ}\text{C}$			1.9	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			30	mA
			$T_{VJ} = -40^{\circ}\text{C}$			50	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}\text{C}$			0.2	V
I_{GD}	gate non-trigger current					1	mA
I_L	latching current	$t_P = 10\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			45	mA
		$I_G = 0.1\text{ A}; di_G/dt = 0.1\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			30	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 0.1\text{ A}; di_G/dt = 0.1\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 5\text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^{\circ}\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 20\text{ V}/\mu\text{s}$ $t_P = 200\text{ }\mu\text{s}$			150		μs

Package TO-263 (D2Pak-HV)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			20	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				1.5		g
F_C	mounting force with clip		20		60	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	4.2			mm
$d_{Spb/Apb}$		terminal to backside	4.7			mm

Product Marking



Part description

C = Thyristor (SCR)
 L = High Efficiency Thyristor
 A = (up to 1200V)
 5 = Current Rating [A]
 E = Single Thyristor
 1200 = Reverse Voltage [V]
 PZ = TO-263AB (D2Pak) (2HV)

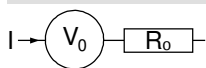
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLA5E1200PZ-TRL	CLA5E1200PZ	Tape & Reel	800	516482
Alternative	CLA5E1200PZ-TUB	CLA5E1200PZ	Tube	50	525276

Similar Part	Package	Voltage class
CLA5E1200UC	TO-252AA (DPak)	1200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150\text{ °C}$

		Thyristor	
$V_{0\text{ max}}$	threshold voltage	0.89	V
$R_{0\text{ max}}$	slope resistance *	82	mΩ

Outlines TO-263 (D2Pak-HV)


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.3		0.091	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

All dimensions conform with and/or within JEDEC standard.



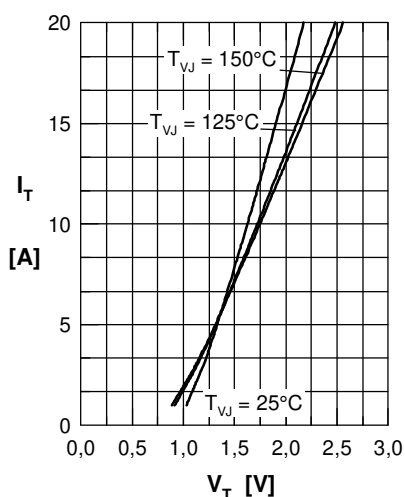
Thyristor


Fig. 1 Forward characteristics

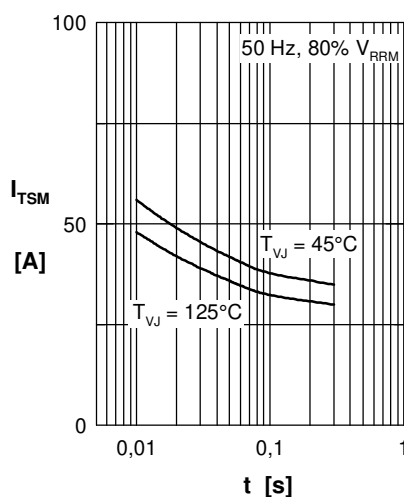
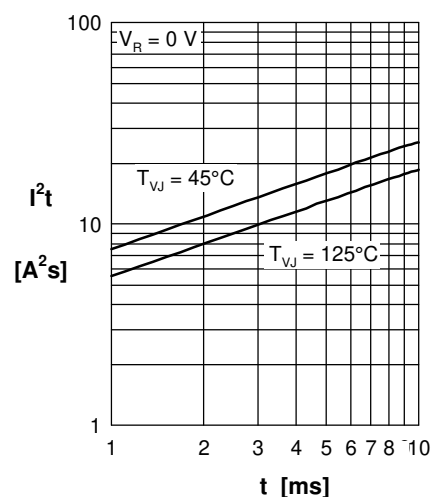
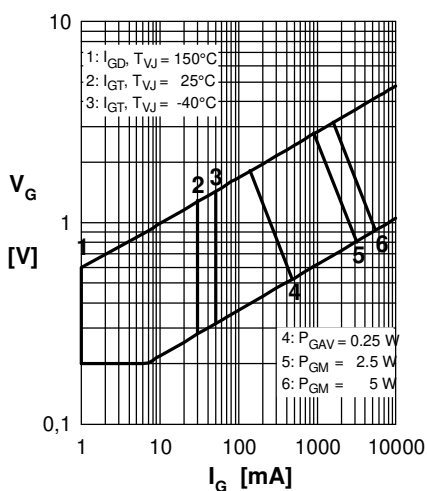

 Fig. 2 Surge overload current
 I_{TSM} : crest value, t : duration

 Fig. 3 I^2t versus time (1-10 s)


Fig. 4 Gate voltage & gate current

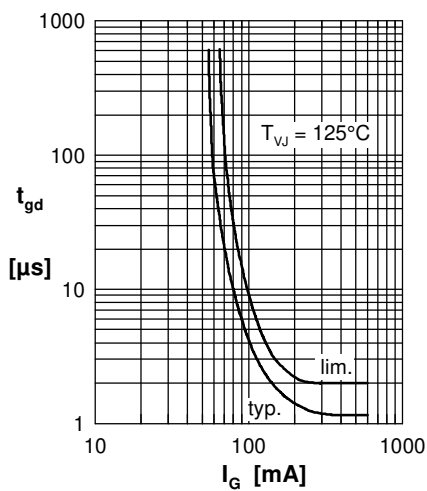
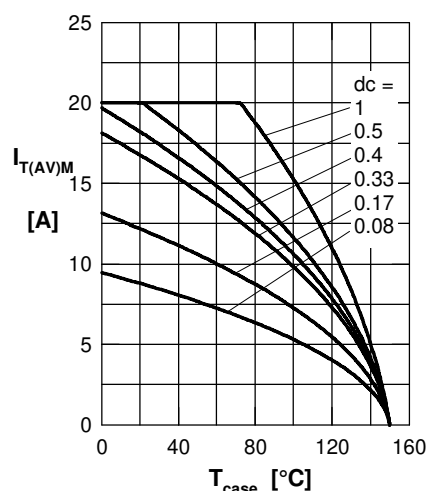

 Fig. 5 Gate controlled delay time t_{gd}


Fig. 6 Max. forward current at case temperature

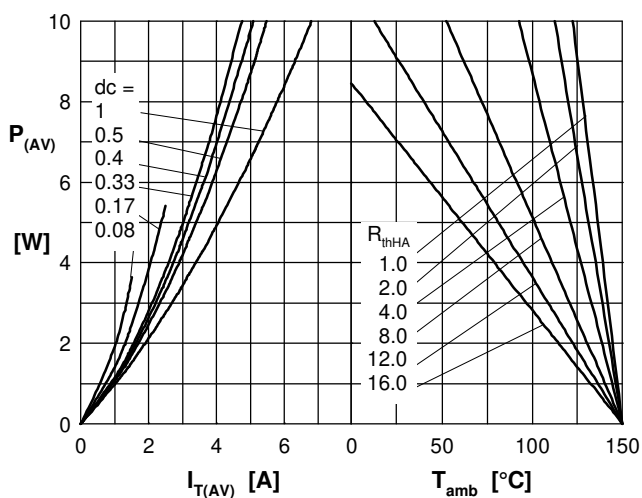
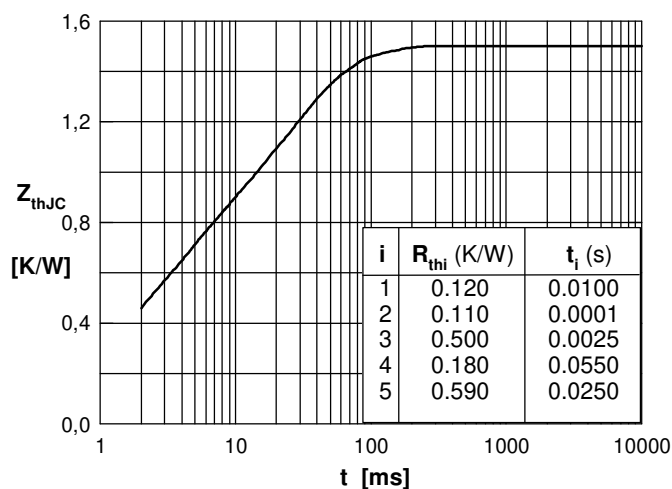

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 7 Transient thermal impedance junction to case